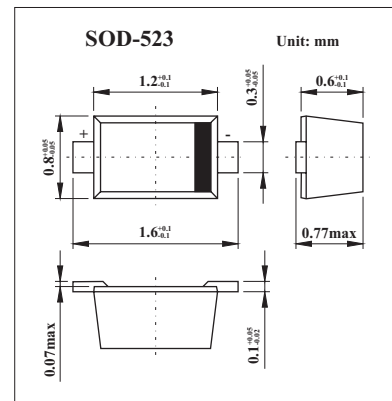


## SCHOTTKY BARRIER DIODE

## 1PS79SB62

## ■ Features

- Ultra high switching speed
- Very low capacitance
- High breakdown voltage
- Guard ring protected
- Ultra small plastic SMD package.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

| Parameter                     | Symbol    | Min | Max  | Unit             |
|-------------------------------|-----------|-----|------|------------------|
| continuous reverse voltage    | $V_R$     |     | 40   | V                |
| continuous forward current    | $I_F$     |     | 20   | mA               |
| storage temperature           | $T_{stg}$ | -65 | +150 | $^\circ\text{C}$ |
| junction temperature          | $T_j$     |     | 125  | $^\circ\text{C}$ |
| operating ambient temperature | $T_{amb}$ | -65 | +150 | $^\circ\text{C}$ |

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

| Parameter                   | Symbol | Conditions                              | Max | Unit           |
|-----------------------------|--------|---|-----|----------------|
| continuous forward voltage  | $V_F$  | $I_F = 2\text{ mA}$ ; note 1            | 800 | mV             |
| capacitance reverse current | $I_R$  | $V_R = 40\text{ V}$ , note              | 1   | $\mu\text{ A}$ |
| diodes capacitance          | $C_d$  | $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$ | 0.6 | pF             |

Note

1. Pulse test: pulse width =  $300\ \mu\text{ s}$ ,  $\delta = 0.02$ .

## ■ Marking

|         |    |
|---------|----|
| Marking | S9 |
|---------|----|